Panasonic

DB2J20900L

Silicon epitaxial planar type

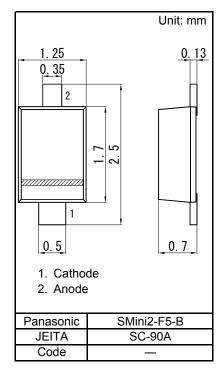
For high frequency rectification DB3X209K in SMini2 type package

■ Features

- · Low forward voltage VF
- · Short reverse recovery time trr
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: BE

■ Packaging

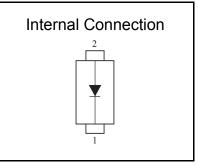
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



■ Absolute Maximum Ratings Ta = 25 °C

| Parameter | Symbol | Rating | Unit | | | |
|----------------------------------------------|--------|-------------|------|--|--|--|
| Reverse voltage | VR | 20 | V | | | |
| Repetitive peak reverse voltage | VRRM | 20 | V | | | |
| Forward current (Average) | IF(AV) | 500 | mA | | | |
| Non-repetitive peak forward surge current *1 | IFSM | 3 | Α | | | |
| Junction temperature | Tj | 125 | °C | | | |
| Operating ambient temperature | Topr | -40 to +85 | °C | | | |
| Storage temperature | Tstg | -55 to +125 | °C | | | |
| A 1 (A) | | | | | | |

Note: *1 50Hz sine wave 1 cycle (Non-repetitive peak current)



Schottky Barrier Diode

DB2J20900L

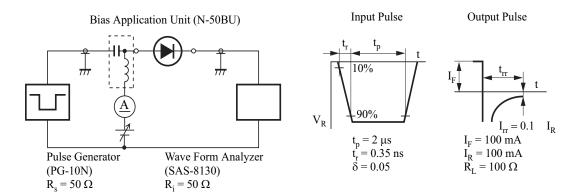
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■ Electrical Characteristics Ta = 25 °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--------------------------|--------|-------------------------------------------|-----|-----|-----|------|
| Forward voltage | VF1 | IF = 10 mA | | | 0.3 | V |
| | VF2 | IF = 500 mA | | | 0.5 | |
| Reverse current | IR | VR = 10 V | | | 30 | μΑ |
| Terminal capacitance | Ct | VR = 10 V, f = 1 MHz | | 7 | | pF |
| Reverse recovery time *1 | trr | IF = IR = 100 mA, | 2.4 | | no | |
| | uı | Irr = $0.1 \times IR$, RL = 100Ω | | 2.4 | | ns |

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

- 2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.
- 3. Absolute frequency of Input and output is 400 MHz.
- 4. *1 : trr measurement circuit

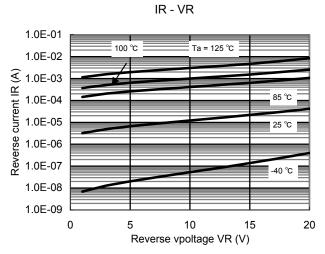


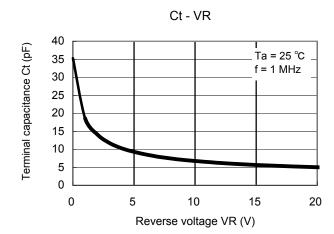
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Schottky Barrier Diode DB2J20900L

Technical Data (reference)

IF - VF 1.0E+00 1.0E-01 Fpward current IF (A) 1.0E-02 1.0E-03 1.0E-04 1.0E-05 0.1 0.6 0.0 0.2 0.3 0.4 0.5 Forward voitage VF (V)





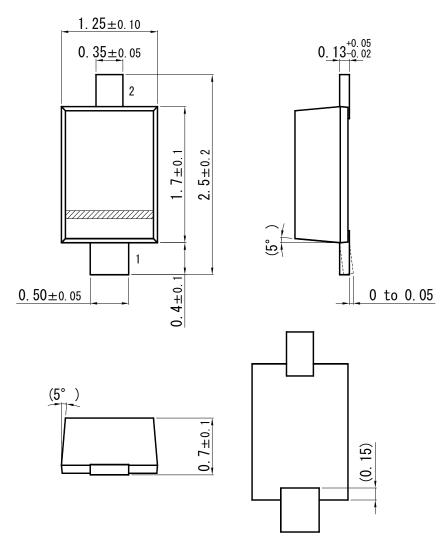
Schottky Barrier Diode

DB2J20900L

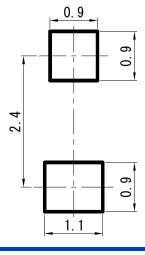
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SMini2-F5-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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